

	Type	Hits	Search Text	DBs
1	IS&R	1468	(438/602,167-189).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	BRS	2	"59214224"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
3	BRS	468	(Schottky or non-ohmic or ("not" or non) adj ohmic)) near15 ((silicon adj carbide) or SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	BRS	342	((Schottky or non-ohmic or ("not" or non) adj ohmic)) near15 ((silicon adj carbide) or SiC) and @ad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
5	BRS	86	((Schottky or non-ohmic or ("not" or non) adj ohmic)) near15 ((silicon adj carbide) or SiC) and @rlad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	BRS	367	((((Schottky or non-ohmic or ("not" or non) adj ohmic)) near15 ((silicon adj carbide) or SiC)) and @ad<"20011220") (((Schottky or non-ohmic or ("not" or non) adj ohmic)) near15 ((silicon adj carbide) or SiC)) and @rlad<"20011220")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7	BRS	425997	(heat\$5 or aneal\$5) near15 (Schottky or non-ohmic or ("not" or non) adj ohmic) or metal or al aluminum or zn or zinc)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
8	BRS	70	(((((Schottky or non-ohmic or ("not" or non) adj ohmic))) near15 ((silicon adj carbide) or SiC)) and @ad<"20011220") (((Schottky or non-ohmic or ("not" or non) adj ohmic)) near15 ((silicon adj carbide) or SiC)) and @rlad<"20011220")) and ((heat\$5 or aneal\$5) near15 (Schottky or non-ohmic or ("not" or non) adj ohmic) or metal or al aluminum or zn or zinc))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
9	BRS	0	"6610999".URPN.	USPAT
10	BRS	11	"5789311".URPN.	USPAT
11	BRS	7	("3742317"   "3849789"   "5449925"   "5635412"   "5789311"   "5914500"   "5967795").PN.	USPAT
12	BRS	4	("3663308"   "3897273"   "5270244"   "5399883").PN.	USPAT
13	BRS	20	"5449925".URPN.	USPAT
14	BRS	4	"5502003".URPN.	USPAT
15	BRS	9	"5471072".URPN.	USPAT
16	BRS	17	"5270252".URPN.	USPAT
17	BRS	1218	((438/602,167-189).CCLS.) and @ad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	BRS	429	((438/602,167-189).CCLS.) and @rlad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
19	BRS	1293	((438/602,167-189).CCLS.) and @ad<"20011220") ((438/602,167-189).CCLS.) and @rlad<"20011220")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
20	BRS	154	((438/602,167-189).CCLS.) and @ad<"20011220") ((438/602,167-189).CCLS.) and @rlad<"20011220") and ((aluminum or al) near15 (anneal\$4 or heat\$4 or temperature))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
21	BRS	41	(silicon adj carbide or sic) and (((438/602,167-189).CCLS.) and @ad<"20011220") ((438/602,167-189).CCLS.) and @rlad<"20011220") and ((aluminum or al) near15 (anneal\$4 or heat\$4 or temperature)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
22	BRS	573	ohmic near15 (aluminum or al) and sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
23	BRS	249	(ohmic near15 sic) and (aluminum or al)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
24	BRS	77	((ohmic near15 sic) and (aluminum or al)) and @rlad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
25	BRS	169	((ohmic near15 sic) and (aluminum or al)) and @ad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
26	BRS	196	((((ohmic near15 sic) and (aluminum or al)) and @ad<"20011220") (((ohmic near15 sic) and (aluminum or al)) and @rlad<"20011220")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
27	BRS	0	"20040171204".URPN.	USPAT
28	IS&R	4	((("5376241") or ("5454915")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
29	BRS	177	((((ohmic near15 sic) and (aluminum or al)) and @ad<"20011220") (((ohmic near15 sic) and (aluminum or al)) and @rlad<"20011220")) and (anneal\$4 or heat\$4 or temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
30	BRS	1075241	((anneal\$4 or heat\$4 or temperature) near15 (time or min or minute or minutes or hr or hrs or hour or hours))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
31	BRS	85	(((((ohmic near15 sic) and (aluminum or al)) and @ad<"20011220") (((ohmic near15 sic) and (aluminum or al)) and @rlad<"20011220")) and (anneal\$4 or heat\$4 or temperature) and (((anneal\$4 or heat\$4 or temperature) near15 (time or min or minute or minutes or hr or hrs or hour or hours)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
32	BRS	0	1808682C	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
33	BRS	2	"1808682"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
34	BRS	15426	anneal\$5 near15 (aluminum or al)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
35	BRS	5692	((anneal\$5 near15 (aluminum or al)) same (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
36	BRS	8554	anneal\$5 near7 (aluminum or al)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
37	BRS	3045	((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
38	BRS	1607	((anneal\$5 near7 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
39	BRS	998	((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide o sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
40	BRS	558	((anneal\$5 near7 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide o sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
41	BRS	849	((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide o sic)) and @ad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
42	BRS	292	((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide o sic)) and @rlad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
43	BRS	906	( ((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide o sic)) and @ad<"20011220") ( ((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide o sic)) and @rlad<"20011220")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
44	BRS	460	((anneal\$5 near7 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide o sic)) and @ad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
45	BRS	181	((anneal\$5 near7 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide o sic)) and @rlad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
46	BRS	500	(((((anneal\$5 near7 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide o sic)) and @ad<"20011220") (((anneal\$5 near7 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide o sic)) and @rlad<"20011220")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
47	BRS	117	((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide or sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
48	BRS	70	((anneal\$5 near7 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide or sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB



	Type	Hits	Search Text	DBs
49	BRS	91	((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide or sic)) and @ad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
50	BRS	49	((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide or sic)) and @rlad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
51	BRS	102	((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide or sic)) and @ad<"20011220") (((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide or sic)) and @ad<"20011220") (((anneal\$5 near15 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide or sic)) and @rlad<"20011220")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
52	BRS	52	((anneal\$5 near7 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide or sic)) and @ad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
53	BRS	24	((anneal\$5 near7 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide or sic)) and @rlad<"20011220"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
54	BRS	60	((anneal\$5 near7 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide or sic)) and @ad<"20011220") (((anneal\$5 near7 (aluminum or al)) near15 (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or d or period or time)) and (silicon adj carbide or sic)) and @rlad<"20011220")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
55	BRS	0	(semiconductor adj (resistor or reistors)) and polysilicon near15 (silicon adj carbide or sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
56	BRS	0	(semiconductor adj (resistor or reistors)) and (silicon adj carbide or sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
57	BRS	2	(semiconductor adj (resistor or reistors))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
58	BRS	6	(rapid adj thermal adj annealing) near15 (long adj (period or time))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
59	BRS	1	(aluminum near15 (heat\$4 and anneal\$4)) same ((rta or (rapid near2 (thermal or heating or heat))) or (short near2 (time or duration or period))) same (long near2 (time or duration or period))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
60	BRS	1	(al near15 (heat\$4 and anneal\$4)) same ((rta or (rapid near2 (thermal or heating or heat))) or (short near2 (time or duration or period))) same (long near2 (time or duration or period))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
61	BRS	1	(al near15 (heat\$4 and anneal\$4)) same ((rta or (rapid near2 (thermal or heating or heat))) or (short near2 (time or duration or period or treatment))) same (long near2 (time or duration or period or treatment))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
62	BRS	2761	(al or aluminum) same (low adj temperature) same (high adj temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
63	BRS	25	((al or aluminum) same (low adj temperature) same (high adj temperature)) same (((rapid near2 (thermal or heating or heat))) or (short near2 (time or duration or period or treatment))) same (long near2 (time or duration or period or treatment)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
64	IS&R	2	("6249014").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
65	IS&R	2	("6,613,586").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
66	BRS	64182	(aluminum or al).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
67	BRS	320859	(annealing or heating).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
68	BRS	1060	((aluminum or al).ti.) and ((annealing or heating).ti.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
69	BRS	3	(ohmic adj contact) same (((rapid near2 (thermal or heating or heat))) or (short near2 (time or duration or period or treatment))) same (long near2 (time or duration or period or treatment)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
70	BRS	34	((aluminum or al) near15 reflectivity) same ohmic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
71	IS&R	2	("5250466").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
72	BRS	7	"5250466".URPN.	USPAT
73	IS&R	0	("longnear3anneal\$4near14ohmic").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
74	BRS	3	long near3 anneal\$4 near14 ohmic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
75	BRS	53124	(anneal\$4) near15 ((long near2 (time or duration or period or treatment)) or (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or "d"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
76	BRS	1443	(anneal\$4) near15 (long near2 (time or duration or period or treatment))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
77	BRS	3	((anneal\$4) near15 (long near2 (time or duration or period or treatment)) ) same ohmic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
78	BRS	2	(ohmic adj contact) same ((anneal\$4) near15 (long near2 (time or duration or period or treatment)) )	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
79	BRS	533	(ohmic) same ((anneal\$4) near15 ((long near2 (time or duration or period or treatment)) or (min or mins or minute or minutes or second or seconds or "s" or "sec" or hour or hours or "h" or hr or hrs or day or days or "d"))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
80	BRS	19304	((anneal\$4) near15 (hour or hours or "h" or hr or hrs or day or days or "d"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
81	BRS	113	(ohmic) same ((anneal\$4) near15 (hour or hours or "h" or hr or hrs or day or days or "d"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
82	BRS	325075	(heat\$4) near15 (hour or hours or "h" or hr or hrs or day or days or "d"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
83	BRS	3827	(ohmic) same "40"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
84	BRS	290	(ohmic) same ((heat\$4) near15 (hour or hours or "h" or hr or hrs or day or days or "d"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
85	BRS	17	T-GATE NEAR15 (SILICIDE OR SALICIDE)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
86	BRS	7117	METAL NEAR15 POLYSILICON NEAR15 (SILICIDE OR SALICIDE)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
87	BRS	1027	((forming or depositing) adj3 (metal or conductive or refractory)) same ((forming or depositing) adj3 (polysilicon)) same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
88	BRS	393	((forming or depositing) adj3 (metal or conductive or refractory)) same ((forming or depositing) adj3 (polysilicon)) same gate same (salicide or silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
89	BRS	25	((forming or depositing) adj3 (metal or conductive or refractory)) same ((forming or depositing) adj3 (polysilicon)) same (stack near2 gate) same (salicide or silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
90	BRS	368	((forming or depositing) adj3 (metal or conductive or refractory)) same ((forming or depositing) adj3 (polysilicon)) same gate same (salicide or silicide)) not ((forming or depositing) adj3 (metal or conductive or refractory)) same ((forming or depositing) adj3 (polysilicon)) same (stack near2 gate) same (salicide or silicide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
91	BRS	135	(silicide or salicide) near5 (sige)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
92	IS&R	2	("20030219971").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
93	IS&R	2	("6690072").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
94	IS&R	3355	(438/571,597,602,688,931).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
95	IS&R	0	("landohmic").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
96	BRS	165	S94 and ohmic and (sic or carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB



WPI Acc No: 1999-363161/199931

XRAM Acc No: C99-107279

XRPX Acc No: N99-271169

**Silicon carbide** semiconductor device manufacturing method for power device - involves smoothing **silicon carbide** substrate, after annealing at **high temperature** through alumina film

Patent Assignee: FUJI ELECTRIC CO LTD (FJIE )

Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
JP 11135450	A	19990521	JP 97293720	A	19971027	199931 B

Priority Applications (No Type Date): JP 97293720 A 19971027

Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
JP 11135450	A		4	H01L-021/265	

Abstract (Basic): JP 11135450 A

NOVELTY - The ions are implanted into a **silicon carbide** substrate (1), which is annealed to **high temperature** through a thin alumina film. The substrate is then etched with etching gas, such as hydrogen chloride gas, to make its surface smooth, after removing the alumina film.

USE - For power devices.

ADVANTAGE - Increases carrier mobility of substrate by maintaining its surface smoothness before and after **annealing**, therefore **ohmic metal** electrode **contact** resistance is reduced. Variation in characteristic of element is reduced.

DESCRIPTION OF DRAWING - The figure shows sectional view of processes after ion implantation, annealing and etching. (1) **Silicon-carbide** substrate.

Dwg.1/2

? DS

Set	Items	Description
S1	124	AU=(WOODIN, R? OR WOODIN R?)
S2	127	AU=(SENG, W? OR SENG W?)
S3	249	S1:S2
S4	29	S3 AND (SIC OR (SI OR SILICON OR SILICA) (W) CARBIDE)
S5	4	S4 AND ((OHM OR OHMIC?) (2N) (CONTACT? OR ATTACH? OR CONNECT- ?))
S6	4	RD (unique items)
S7	25	S4 NOT S5
S8	0	S7 AND MELT? (2N) POINT?
S9	8	S7 AND ((HIGH??? OR HEIGHTEN? OR RAIS? OR INCREAS? OR ELEV- AT?) (3N) (TEMPERATUR? OR CELSIUS OR DEGREE? ?))
S10	4	RD (unique items)
S11	17	S7 NOT S9
S12	7	RD (unique items)
S13	241831	SIC OR (SI OR SILICON OR SILICA) (W) CARBIDE
S14	259623	ELECTRIC? (2N) CONNECT?
S15	33772	(OHM OR OHMIC?) (2N) (CONTACT? OR ATTACH? OR CONNECT?)
S16	252083	(HEAT? OR WARM? OR HOT? OR CALEFACT? OR TORREFACT? OR PYRO- L? OR SINTER? OR CALCIN? OR AUTOCLAV? OR ANNEAL?) (2N) METAL?
S17	95328	(THERMOL? OR THERMAL? OR PREHEAT? OR MELT? OR FUSE? OR FUS- ING? ? OR FUSION? OR ANNEAL?) (2N) METAL?
S18	329421	S16:S17
S19	137405	MELT? (2N) POINT?
S20	1871992	(HIGH??? OR HEIGHTEN? OR RAIS? OR INCREAS? OR ELEVAT?) (3N) - (TEMPERATUR? OR CELSIUS OR DEGREE? ?)

S21	1985585	S19:S20
S22	608945	(LONG? OR TIME) (2N) DURAT? OR HOURS
S23	904521	(LOW OR LOWER) (2N) TEMPERATUR?
S24	614	S13 AND S14
S25	14	S24 AND S15
S26	0	S25 AND S18
S27	5	S25 AND S21
S28	5	RD (unique items)
S29	9	S25 NOT S27
S30	9	RD (unique items)
S31	600	S24 NOT S25
S32	9	S31 AND S22
S33	0	S32 AND S23
S34	9	RD S32 (unique items)
S35	591	S31 NOT S32
S36	2226	S13 AND S15
S37	116	S36 AND S18
S38	46	S37 AND S21
S39	10	S38 AND (S22 OR S23)
S40	7	RD (unique items)
S41	36	S38 NOT S39
S42	24	S41 AND S16
S43	23	S42 AND S17
S44	0	S43 AND S19
S45	23	S43 AND S20
S46	16	RD (unique items)
S47	16	S46 NOT S24, S27, S32, S40

(FILE 'HOME' ENTERED AT 10:27:51 ON 24 MAR 2005)

FILE 'REGISTRY' ENTERED AT 10:28:35 ON 24 MAR 2005

L1 1966 S C.SI/MF OR C SI/ELF

FILE 'HCAPLUS' ENTERED AT 10:29:09 ON 24 MAR 2005

L2 84228 S L1 AND (SIC OR (SI OR SILICON OR SILICA) (W) CARBIDE )  
L3 169 S L2 AND ELECTRIC? (2N) CONNECT?  
L4 1 S L3 AND (OHM OR OHMIC?) (2N) (CONTACT? OR ATTACH? OR CONNECT?)  
L5 168 S L3 NOT L4  
L6 4 S L5 AND ((HEAT? OR WARM? OR HOT? OR CALEFACT? OR TORREFACT? OR  
L7 164 S L5 NOT L6  
L8 2 S L7 AND ((THERMOL? OR THERMAL? OR PREHEAT? OR MELT? OR FUSE? O  
L9 162 S L7 NOT L8  
L10 13 S L9 AND ((HIGH? OR HEIGHTEN? OR RAIS? OR INCREAS? OR ELEVAT?) (  
L11 13 DUP REM L10 (0 DUPLICATES REMOVED)  
L12 149 S L9 NOT L10  
L13 0 S L12 AND MELT? (2N) POINT?  
L14 0 S L12 AND ((LONG? OR TIME) (2N) DURAT? OR HOURS)  
L15 1 S L12 AND (LOW OR LOWER) (2N) TEMPERATUR?  
L16 582 S L2 AND (OHM OR OHMIC?) (2N) (CONTACT? OR ATTACH? OR CONNECT?)  
L17 25 S L16 AND ((HEAT? OR WARM? OR HOT? OR CALEFACT? OR TORREFACT? O  
L18 0 S L17 AND MELT? (2N) POINT?  
L19 9 S L17 AND ((HIGH? OR HEIGHTEN? OR RAIS? OR INCREAS? OR ELEVAT?)  
L20 9 DUP REM L19 (0 DUPLICATES REMOVED)  
L21 9 S L20  
L22 9 S L20 NOT L4, L8, L10, L15  
L23 16 S L17 NOT L19  
L24 1 S L23 AND (LOW OR LOWER) (2N) TEMPERATUR?  
L25 15 S L23 NOT L24  
L26 0 S L25 AND ((LONG? OR TIME) (2N) DURAT? OR HOURS)  
L27 15 S L25  
L28 557 S L16 NOT L17  
L29 0 S S28 AND MELT? (2N) POINT?  
L30 1 S S28 AND MELT?

L4 ANSWER 1 OF 1 HCAPLUS COPYRIGHT 2005 ACS on STN

AN 2004:240337 HCAPLUS Full-text

DN 141:149287

TI Measuring system with semiconductor transducer built around  
**silicon carbide** Schottky barrier diodes

IN Afanas'ev, A. V.; Il'in, V. A.; Petrov, A. A.

PA Russia

SO Russ., No pp. given

CODEN: RUXXE7

DT Patent

LA Russian

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI	RU 2224332	C1	20040220	RU 2002-119492	20020717
PRAI	RU 2002-119492		20020717		

AB Temperature and/or UV radiation measuring systems using a single transducer  
for measurements at high temps. are described which employ a transducer based